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4. (Once amended) A method for improving the charge retention in a nitride layer of a memory cell, said method comprising:

depositing a nitride layer; and
introducing oxygen into substantially all of said nitride layer within said memory cell,
so as to enhance charge retention within said nitride layer.

5. (Once amended) A method for improving the charge retention in a nitride layer of a memory cell, said method comprising:

depositing a nitride layer;
controlling the thickness of said deposited nitride layer; and
introducing oxygen into substantially all of said nitride layer within said memory cell,
so as to enhance charge retention within said nitride layer.

7. A method of manufacturing a programmable, read only memory device, the method comprising:

forming a first oxide layer on a substrate,
forming a nitride layer on top of said oxide layer, wherein said nitride layer is 150 angstroms or less thick;
introducing oxygen into substantially all of said nitride layer within a memory cell during formation of a second oxide layer on top of said nitride layer, so as to enhance charge retention within said nitride layer;
patterning said oxide-nitride-oxide (ONO) layers into desired patterns; and
forming a gate layer over said patterned ONO layer.

REMARKS

The present amendment is intended to be fully responsive to all points of rejection raised by the Examiner in the parent application and is believed to place the application in condition for allowance. Favorable reconsideration and allowance of the application is respectfully requested.

Applicant asserts that the present invention is new, non-obvious and useful. Prompt reconsideration and allowance of the claims is respectfully requested.